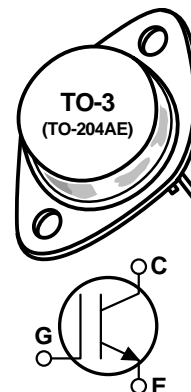


## Thunderbolt IGBT™

The Thunderbolt IGBT™ is a new generation of high voltage power IGBTs. Using Non-Punch Through Technology the Thunderbolt IGBT™ offers superior ruggedness and ultrafast switching speed.

- Low Forward Voltage Drop
- Low Tail Current
- Avalanche Rated
- Hermetic Package
- High Freq. Switching to 150KHz
- Ultra Low Leakage Current
- RBSOA and SCSOA Rated




### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT30GT60AR	UNIT
$V_{CES}$	Collector-Emitter Voltage	600	Volts
$V_{CGR}$	Collector-Gate Voltage ( $R_{GE} = 20K\Omega$ )	600	
$V_{EC}$	Emitter-Collector Voltage	15	
$V_{GE}$	Gate-Emitter Voltage	$\pm 20$	
$I_{C1}$	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	40	Amps
$I_{C2}$	Continuous Collector Current @ $T_C = 90^\circ\text{C}$	30	
$I_{CM}$	Pulsed Collector Current <sup>(1)</sup> @ $T_C = 25^\circ\text{C}$	80	
$I_{LM}$	RBSOA Clamped Inductive Load Current @ $R_g = 11\Omega$ $T_C = 125^\circ\text{C}$	60	
$E_{AS}$	Single Pulse Avalanche Energy <sup>(2)</sup>	65	mJ
$P_D$	Total Power Dissipation	160	Watts
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 0.5mA, T_J = -55^\circ\text{C}$ )	600			Volts
$RBV_{CES}$	Collector-Emitter Reverse Breakdown Voltage ( $V_{GE} = 0V, I_C = 50mA$ )	-15			
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 700\mu A, T_J = 25^\circ\text{C}$ )	3	4	5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = I_{C2}, T_J = 25^\circ\text{C}$ )	1.6	2.0	2.5	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = I_{C2}, T_J = 150^\circ\text{C}$ )			2.8	
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 25^\circ\text{C}$ )			40	$\mu A$
	Collector Cut-off Current ( $V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 150^\circ\text{C}$ )			1000	
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V, V_{CE} = 0V$ )			$\pm 100$	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

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**DYNAMIC CHARACTERISTICS**
**APT30GT60AR**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$C_{ies}$	Input Capacitance	<b>Capacitance</b> $V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1\text{ MHz}$		1600		pF
$C_{oes}$	Output Capacitance			155		
$C_{res}$	Reverse Transfer Capacitance			90		
$Q_g$	Total Gate Charge <sup>③</sup>	<b>Gate Charge</b> $V_{GE} = 15V$ $V_{CC} = 0.5V_{CES}$ $I_C = I_{C2}$		140		nC
$Q_{ge}$	Gate-Emitter Charge			60		
$Q_{gc}$	Gate-Collector ("Miller") Charge			12		
$t_{d(on)}$	Turn-on Delay Time	<b>Resistive Switching (25°C)</b> $V_{GE} = 15V$ $V_{CC} = 0.8V_{CES}$ $I_C = I_{C2}$ $R_G = 10\Omega$		14		ns
$t_r$	Rise Time			55		
$t_{d(off)}$	Turn-off Delay Time			190		
$t_f$	Fall Time			140		
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (150°C)</b> $V_{CLAMP(Peak)} = 0.66V_{CES}$ $V_{GE} = 15V$ $I_C = I_{C2}$ $R_G = 10\Omega$ $T_J = +150^\circ\text{C}$		18		ns
$t_r$	Rise Time			30		
$t_{d(off)}$	Turn-off Delay Time			300		
$t_f$	Fall Time			25		
$E_{on}$	Turn-on Switching Energy	$R_G = 10\Omega$ $T_J = +150^\circ\text{C}$		0.5		mJ
$E_{off}$	Turn-off Switching Energy			1.2		
$E_{ts}$	Total Switching Losses			1.7		
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (25°C)</b> $V_{CLAMP(Peak)} = 0.66V_{CES}$ $V_{GE} = 15V$ $I_C = I_{C2}$ $R_G = 10\Omega$ $T_J = +25^\circ\text{C}$		18		ns
$t_r$	Rise Time			30		
$t_{d(off)}$	Turn-off Delay Time			260		
$t_f$	Fall Time			20		
$E_{ts}$	Total Switching Losses			1.3		
gfe	Forward Transconductance	$V_{CE} = 20V, I_C = I_{C2}$	6			S

**THERMAL CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.78	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

②  $I_C = I_{C2}, R_{GE} = 25\Omega, L = 144\mu\text{H}, T_J = 25^\circ\text{C}$

③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.



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